



《风光欣》技术资料

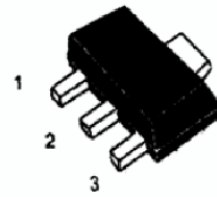
2SD965

NPN TRANSISTOR

ABSOLUTE MAXIMUM RATINGS(TA=25)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CBO}	42	V
Collector-Emitter Voltage	V _{CEO}	22	V
Emitter -Base Voltage	V _{EBO}	7	V
Collector Current	I _{cm}	5	A
Collector Dissipation	P _c	750	mW
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~ +150	

SOT-89



1,Base 2,Collector 3, Emitter

ELECTRICAL CHARACTERISTICS(TA=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = 100 μ A,I _E =0	40			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = 1mA,I _B =0	20			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E = 50 μ A,I _C =0	7			V
Collector Cut-off Current	I _{CBO}	V _{CB} = 20V,I _E =0			100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 7V,I _C =0,			100	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 3A,I _B =0.1A			1.0	V
DC Current Gain	h _{FE}	V _{CE} = 2V,I _C =100mA,	180		600	
Transition frequency	f _T	V _{CE} = 2V,I _C = 500mA		150		MHZ
Output Capacitance	C _{OB}	V _{CB} = 10V,I _E = 0,f=1MHZ		25		pF

h_{FE} CLASSIFICATION

Ltem	P	Q	R	S
HFE	180~270	230~380	340~600	580~900